

CONFIRMED PLENARY AND INVITED SPEAKERS		
Authors	Affiliation	Title
Todd Bauer	DARPA	Review of DARPA's T-MUSIC Program
Yves Gigase	Chips Joint Undertaking	The European Chips Act
Hoi Lee	University of Texas, Dallas	High-efficiency high-conversion-ratio power delivery circuits for computing applications
Steven Callender	Intel	D-Band meets FinFET: Fully-Integrated Transmitter and Receiver Architectures for 100+ Gb/s Links
Eric Bryerton	Virginia Diode	Trends in mmW & THz Test Equipment
Teruo Jyo,	NTT	300-GHz-Band InP HBT Power Amplifier and InP-CMOS
Munehiko Nagakani		Hybrid Phased-Array Transmitter
Alyosha C. Molnar	Cornell University	N-path mixers beyond CMOS
Pascal Chevalier	ST Microelectronics	A 55-nm Flexible SiGe BiCMOS Technology for Wired, Wireless, and Satcom Applications
Takuya Maeda	University of Tokyo	Characterization of ScAlN/GaN Toward Electronic Device Application
Trevor Thornton	Arizona State University	Diamond-BN Heterojunctions for High Power Devices: The Ultimate HEMT?
Jim Sowers	Maxar Space Infrastructure	III-V Semiconductors in Commercial Communication Satellite Payloads
Kenle Chen	University of Central Florida	Load Modulated Balanced Amplifiers for Next-G Wireless Communications
Bernhard Grote	NXP	Advances in GaN HEMT and GaN PA techniques for base-stations
Lan Wei	University of Waterloo	A Family of Physics-Based Models for Monolithic GaN Integration
Larry Dunleavy	Modelithics Inc., University of South Florida	Practical Dimensions on Contemporary GaN HEMT Modeling
Alexander Rylyakov	Nokia	Next Generation Optical Transceiver for Data Center Interconnect
Christian Reimer	Hyperlight	Integrated Photonics in Thin-Film Lithium Niobate
Tsunenobu Kimoto	Kyoto University	SiC based power devices for extreme temp operations
Zlatan Stanojevic	Global TCAD	Process to Parasitics Simulations
Randy Wolf	GlobalFoundries	State of the Art in PA Design for Wireless applications - Opportunities and challenges for compact modeling